

REMARKS

Claims 1-20 are now present in this application.

The specification and claim 1 have been amended, claim 20 has been presented, and claims 12-19 are currently withdrawn from consideration. Reconsideration of the application, as amended, is respectfully requested.

Rejection under 35 USC 102(e)

Claims 1-11 stand rejected under 35 USC 102(e) as being anticipated by JOHNSON, US Patent 6,525,953. This rejection is respectfully traversed.

It is noted that independent claim 1 has been amended, to delete the term "part of" after "a plurality of dielectric layers on." Support for this amendment can be found on page 12, line 29, page 13, lines 1-2, and Figs. 11, 2, 3p, and 4 of the originally filed application. It is therefore respectfully submitted that no new matter is present.

Independent claim 1 recites a mask read only memory containing vertical diodes. Specifically, in the presently claimed invention, dielectric layers are formed on the top surface of some diodes and second conductive lines are formed on the top surface of the other diodes. Namely, the vertical diodes are sorted by whether there is a dielectric layer thereon. The diodes having the dielectric layer thereon are defined as a first logic state, for example a logic "0", and the diodes without the dielectric layer thereon are defined as a second logic state, for example a logic "1". The Examiner's attention is drawn to page 12, line 29, page 13, lines 1-2, page 13, lines 13-15, page 21, lines 9-12,

page 22, lines 19-30, page 23, lines 1-3, and Figs. 1l, 2, 3p, and 4 of the originally filed application.

Independent claim 20 clearly identifies that the claimed mask read only memory comprises first diodes with dielectric layer directly formed thereon, and second diodes with dielectric layer directly formed thereon. Support for this newly present claim can be found on page 12, lines 13-29, page 13, lines, 1-16, page 21, lines 4-30, page 22, lines 1-6 and Figs. 1l, 2, 3p, and 4 of the originally filed application. It is therefore respectfully submitted that the addition of this claim does not contain any new matter.

JOHNSON discloses a memory cell comprising diodes. JOHNSON teaches forming a disrupted dielectric layers to separate first and second diode components (i.e. p-type and n-type conductive layer). Namely, the dielectric layer is formed among the diode, rather than forming outside the diodes as cited in independent claims 1 and 20. It is respectfully submitted that JOHNSON fails to teach or suggest any dielectric layer formed directly on any diodes.

In view of the foregoing amendments and remarks, it is respectfully submitted that the prior art utilized by the Examiner fails to teach or suggest independent claims 1 and 20, as well as their dependent claims. Accordingly, reconsideration and withdrawal of the 35 USC 102(e) rejection are respectfully requested.

Conclusion

Favorable reconsideration and an early Notice of Allowance are earnestly solicited.

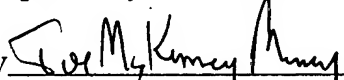
In the event that any outstanding matters remain in this application, the Examiner is invited to contact the undersigned at (703) 205-8000 in the Washington, D.C. area.

Pursuant to 37 C.F.R. §§ 1.17 and 1.136(a), the Applicants respectfully petition for a one (1) month extension of time for filing a response in connection with the present application and the required fee of \$110.00 is attached herewith.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

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Respectfully submitted,

By 

Joe McKinney Muncy

Registration No.: 32,334

BIRCH, STEWART, KOLASCH & BIRCH, LLP

8110 Gatehouse Rd

Suite 100 East

P.O. Box 747

Falls Church, Virginia 22040-0747

(703) 205-8000

Attorney for Applicant